- **Operates With 3-V to 5.5-V V_{CC} Supply**
- **Operates Up To 1 Mbit/s**
- **Low Standby Current . . . 1 μA Typ**
- **External Capacitors . . . 4 × 0.1 μF**
- **Accepts 5-V Logic Input With 3.3-V Supply**
- **RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)**
- **Applications**
  - **Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment**

DB, DW, OR PW PACKAGE
(TOP VIEW)

$\overline{EN}$	1	20	$\overline{PWRDOWN}$
C1+	2	19	V_{CC}
V+	3	18	GND
C1−	4	17	DOUT1
C2+	5	16	RIN1
C2−	6	15	ROUT1
V−	7	14	NC
DOUT2	8	13	DIN1
RIN2	9	12	DIN2
ROUT2	10	11	NC
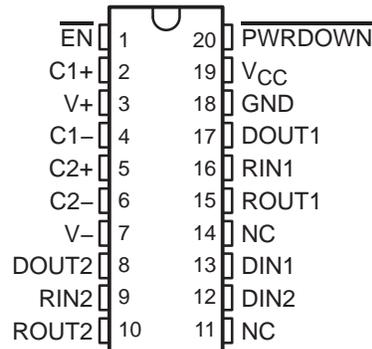
NC – No internal connection

description/ordering information

The SN65C3222 and SN75C3222 consist of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). The devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 24 V/μs to 150 V/μs.

The SN65C3222 and SN75C3222 can be placed in the power-down mode by setting $\overline{PWRDOWN}$ low, which draws only 1 μA from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled, V+ is lowered to V_{CC}, and V− is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting $\overline{EN}$ high.

ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
−0°C to 70°C	SOIC (DW)	Tube of 25	SN75C3222DW	75C3222
		Reel of 2000	SN75C3222DWR	
	SSOP (DB)	Reel of 2000	SN75C3222DBR	CA3222
	TSSOP (PW)	Tube of 70	SN75C3222PW	CA3222
		Reel of 2000	SN75C3222PWR	
−40°C to 85°C	SOIC (DW)	Tube of 25	SN65C3222DW	65C3222
		Reel of 2000	SN65C3222DWR	
	SSOP (DB)	Reel of 2000	SN65C3222DBR	CB3222
	TSSOP (PW)	Tube of 70	SN65C3222PW	CB3222
		Reel of 2000	SN65C3222PWR	

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TEXAS INSTRUMENTS

Function Tables

EACH DRIVER

INPUTS		OUTPUT
DIN	$\overline{\text{PWRDOWN}}$	**DOUT**
X	L	Z
L	H	H
H	H	L

H = high level, L = low level, X = irrelevant,
Z = high impedance

EACH RECEIVER

INPUTS		OUTPUT
RIN	$\overline{\text{EN}}$	**ROUT**
L	L	H
H	L	L
X	H	Z
Open	L	H

H = high level, L = low level, X = irrelevant,
Z = high impedance (off), Open = input
disconnected or connected driver off

logic diagram (positive logic)
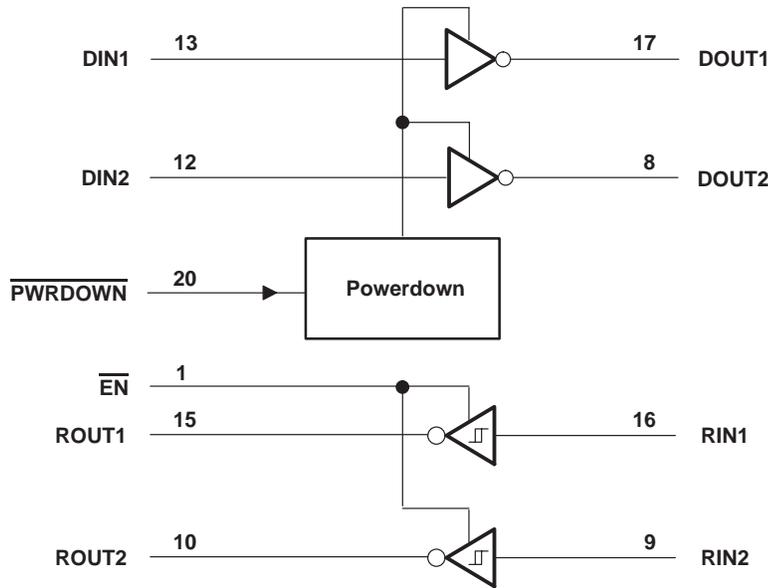
absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} (see Note 1) .... −0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1) .... −0.3 V to 7 V
Negative output supply voltage range, V− (see Note 1) .... 0.3 V to −7 V
Supply voltage difference, V+ − V− (see Note 1) .... 13 V
Input voltage range, V_I: Drivers, $\overline{EN}$, $\overline{PWRDOWN}$ .... −0.3 V to 6 V
                Receivers .... −25 V to 25 V
Output voltage range, V_O: Drivers .... −13.2 V to 13.2 V
                Receivers .... −0.3 V to V_{CC} + 0.3 V
Package thermal impedance, θ_{JA} (see Notes 2 and 3): DB package .... 70°C/W
                                DW package .... 58°C/W
                                PW package .... 83°C/W
Operating virtual junction temperature, T_J .... 150°C
Storage temperature range, T_{stg} .... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
NOTES: 1. All voltages are with respect to network GND.
      2. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) − T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
      3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4 and Figure 5)

				MIN	NOM	MAX	UNIT
	Supply voltage	V_{CC} = 3.3 V		3	3.3	3.6	V
		V_{CC} = 5 V		4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$				0.8	V
V_I	Driver and control input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$		0		5.5	V
V_I	Receiver input voltage			−25		25	V
T_A	Operating free-air temperature	SN65C3222		−40		85	°C
		SN75C3222		0		70	

NOTE 4: Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
I_I	Input leakage current ($\overline{EN}$, $\overline{PWRDOWN}$)			±0.01	±1	µA
I_{CC}	Supply current	No load, $\overline{PWRDOWN}$ at V_{CC}		0.3	1	mA
	Supply current (powered off)	No load, $\overline{PWRDOWN}$ at GND		1	10	µA

‡ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
NOTE 4: Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

TEXAS INSTRUMENTS

DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

	PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = V_{CC}	–5	–5.4		V
I_{IH}	High-level input current	$V_I = V_{CC}$			±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND			±0.01	±1	µA
I_{OS}	Short-circuit output current‡	V_{CC} = 3.6 V,	V_O = 0 V		±35	±60	mA
		V_{CC} = 5.5 V,	V_O = 0 V		±35	±90	
r_o	Output resistance	V_{CC}, V+, and V– = 0 V,	$V_O = ±2$ V	300	10M		Ω
I_{off}	Output leakage current	$\overline{PWRDOWN}$ = GND	$V_O = ±12$ V, V_{CC} = 3 V to 3.6 V			±25	µA
			$V_O = ±10$ V, V_{CC} = 4.5 V to 5.5 V			±25	

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
‡ Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.
NOTE 4:   Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
	Maximum data rate (see Figure 1)	R_L = 3 kΩ, One DOUT switching	C_L = 1000 pF	250			kbit/s
			C_L = 250 pF, V_{CC} = 3 V to 4.5 V	1000			
			C_L = 1000 pF, V_{CC} = 4.5 V to 5.5 V	1000			
$t_{sk(p)}$	Pulse skew§	C_L = 150 pF to 2500 pF	R_L = 3 kΩ to 7 kΩ, See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	R_L = 3 kΩ to 7 kΩ, V_{CC} = 3.3 V	C_L = 150 pF to 1000 pF	18		150	V/µs

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
§ Pulse skew is defined as $|t_{PLH} – t_{PHL}|$ of each channel of the same device.
NOTE 4:   Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	$I_{OH} = -1$ mA	$V_{CC} - 0.6$ V	$V_{CC} - 0.1$ V		V
V_{OL}	Low-level output voltage	$I_{OL} = 1.6$ mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	$V_{CC} = 3.3$ V		1.5	2.4	V
		$V_{CC} = 5$ V		1.8	2.4	
V_{IT-}	Negative-going input threshold voltage	$V_{CC} = 3.3$ V	0.6	1.2		V
		$V_{CC} = 5$ V	0.8	1.5		
V_{hys}	Input hysteresis ($V_{IT+} - V_{IT-}$)			0.3		V
I_{off}	Output leakage current	$\overline{EN} = V_{CC}$		±0.05	±10	µA
r_i	Input resistance	$V_I = \pm3$ V to ±25 V	3	5	7	kΩ

† All typical values are at $V_{CC} = 3.3$ V or $V_{CC} = 5$ V, and $T_A = 25°C$.
NOTE 4: Test conditions are C1–C4 = 0.1 µF at $V_{CC} = 3.3$ V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at $V_{CC} = 5$ V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	$C_L = 150$ pF, See Figure 3		300		ns
t_{PHL}	Propagation delay time, high- to low-level output	$C_L = 150$ pF, See Figure 3		300		ns
t_{en}	Output enable time	$C_L = 150$ pF, $R_L = 3$ kΩ, See Figure 4		200		ns
t_{dis}	Output disable time	$C_L = 150$ pF, $R_L = 3$ kΩ, See Figure 4		200		ns
$t_{sk(p)}$	Pulse skew‡	See Figure 3		300		ns

† All typical values are at $V_{CC} = 3.3$ V or $V_{CC} = 5$ V, and $T_A = 25°C$.
‡ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
NOTE 4: Test conditions are C1–C4 = 0.1 µF at $V_{CC} = 3.3$ V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at $V_{CC} = 5$ V ± 0.5 V.

PARAMETER MEASUREMENT INFORMATION

$$SR(tr) = \frac{6\ V}{t_{THL}\ or\ t_{TLH}}$$
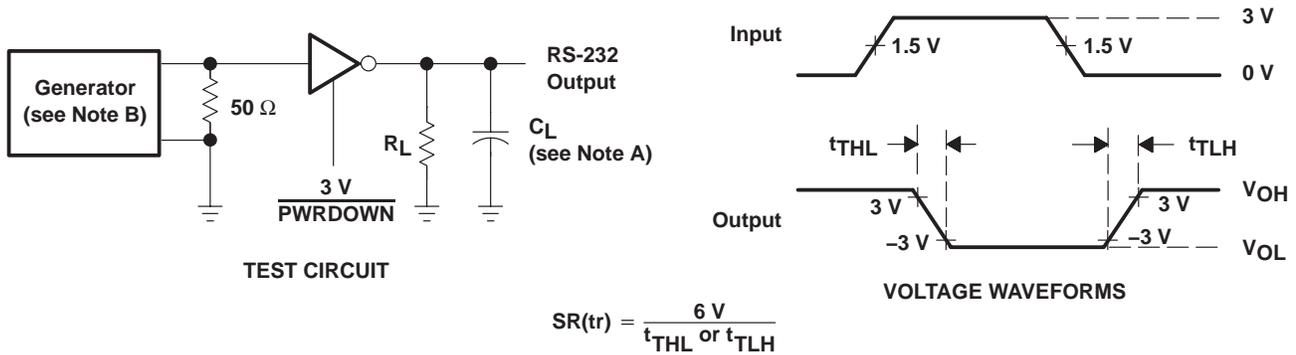
NOTES: A. C_L includes probe and jig capacitance.
        B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \leq$ 10 ns, $t_f \leq$ 10 ns.

Figure 1. Driver Slew Rate
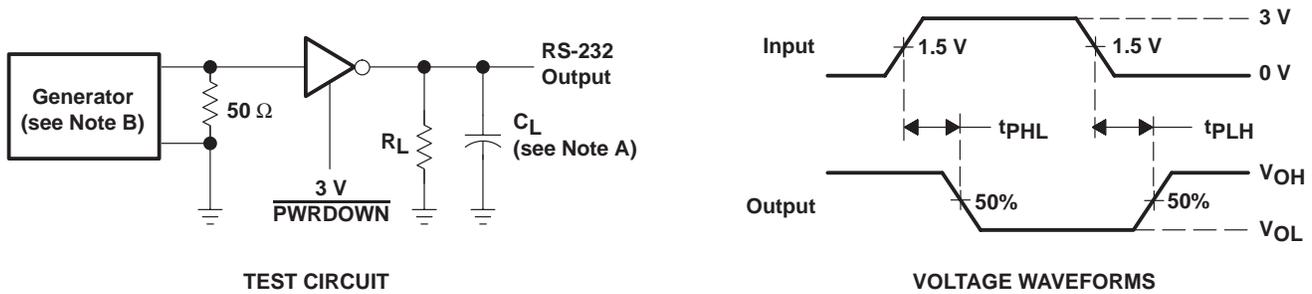

NOTES: A. C_L includes probe and jig capacitance.
        B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \leq$ 10 ns, $t_f \leq$ 10 ns.

Figure 2. Driver Pulse Skew
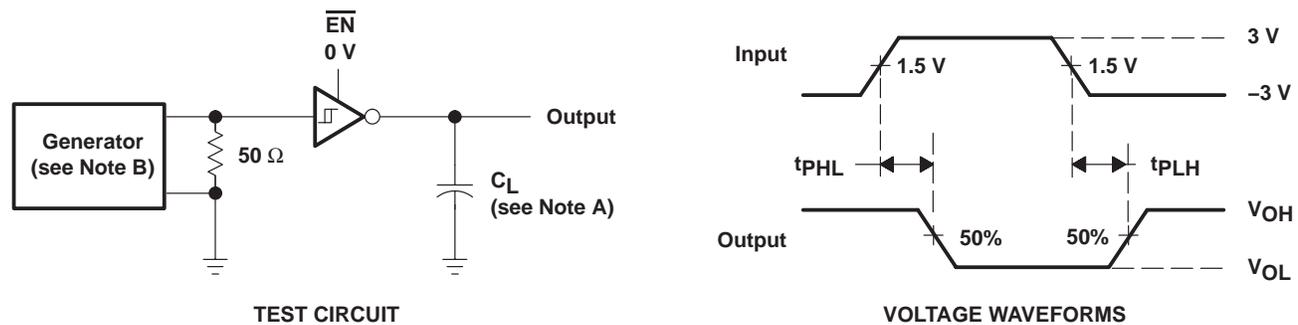
NOTES: A. C_L includes probe and jig capacitance.
        B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \leq$ 10 ns, $t_f \leq$ 10 ns.

Figure 3. Receiver Propagation-Delay Times

PARAMETER MEASUREMENT INFORMATION
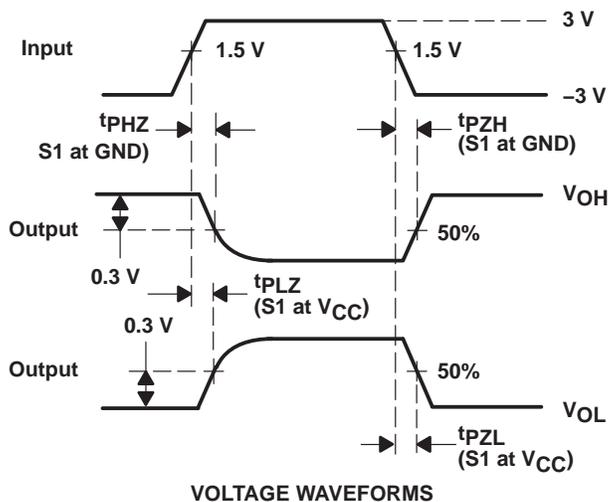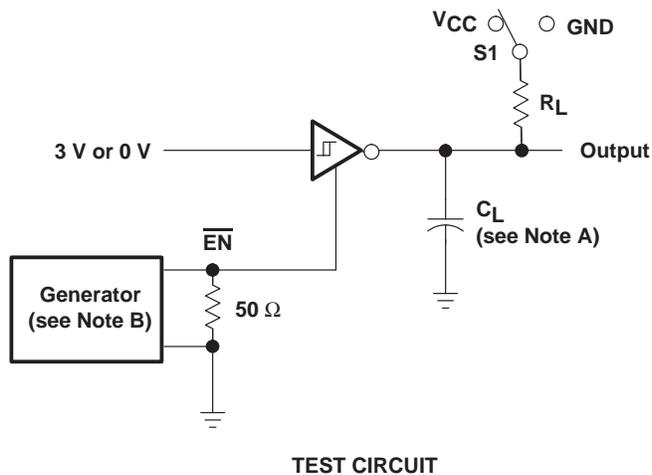
TEST CIRCUIT

VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns.

Figure 4. Receiver Enable and Disable Times

APPLICATION INFORMATION
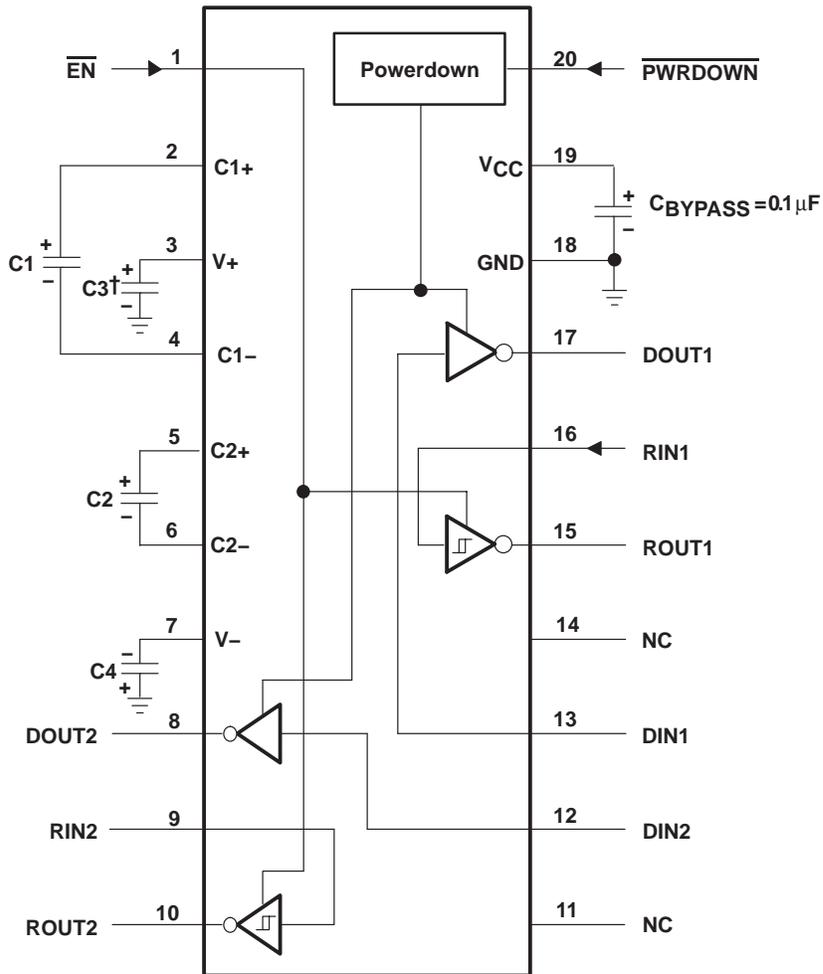
† C3 can be connected to V_{CC} or GND.
NOTES: A. Resistor values shown are nominal.
        B. NC – No internal connection

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.3 V	0.1 μF	0.1 μF
5 V ± 0.5 V	0.047 μF	0.33 μF
3 V to 5.5 V	0.1 μF	0.47 μF

Figure 5. Typical Operating Circuit and Capacitor Values

TEXAS
INSTRUMENTS
POST OFFICE BOX 655303 ● DALLAS, TEXAS 75265

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C3222DBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222	Samples
SN65C3222DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222	Samples
SN65C3222PW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222	Samples
SN65C3222PWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222	Samples
SN75C3222DW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222	Samples
SN75C3222DWG4	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222	Samples
SN75C3222DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222	Samples
SN75C3222PW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3222	Samples
SN75C3222PWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3222	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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![Texas Instruments logo]

PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

Reel Diameter

Reel Width (W1)

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

Sprocket Holes

User Direction of Feed

Pocket Quadrants

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3222DBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3222DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN65C3222PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN75C3222DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN75C3222PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS
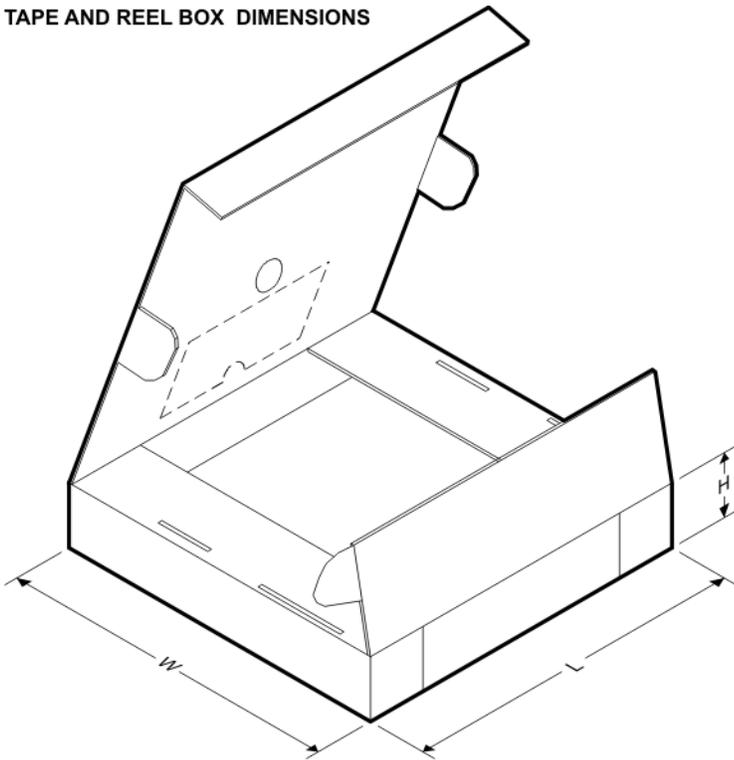
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3222DBR	SSOP	DB	20	2000	853.0	449.0	35.0
SN65C3222DWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN65C3222PWR	TSSOP	PW	20	2000	853.0	449.0	35.0
SN75C3222DWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN75C3222PWR	TSSOP	PW	20	2000	853.0	449.0	35.0

8.2 / 7.4 TYP

A

PIN 1 INDEX AREA

1

20

18X 0.65

7.5 / 6.9 NOTE 3

2X 5.85

10

11

20X 0.38 / 0.22

⊕ 0.1 Ⓜ C A B

B

5.6 / 5.0 NOTE 4

C

◯ 0.1 C

SEATING PLANE

SEE DETAIL A

(0.15) TYP

GAGE PLANE

0.25

0°-8°

0.95 / 0.55

2 MAX

0.05 MIN

DETAIL A
TYPICAL
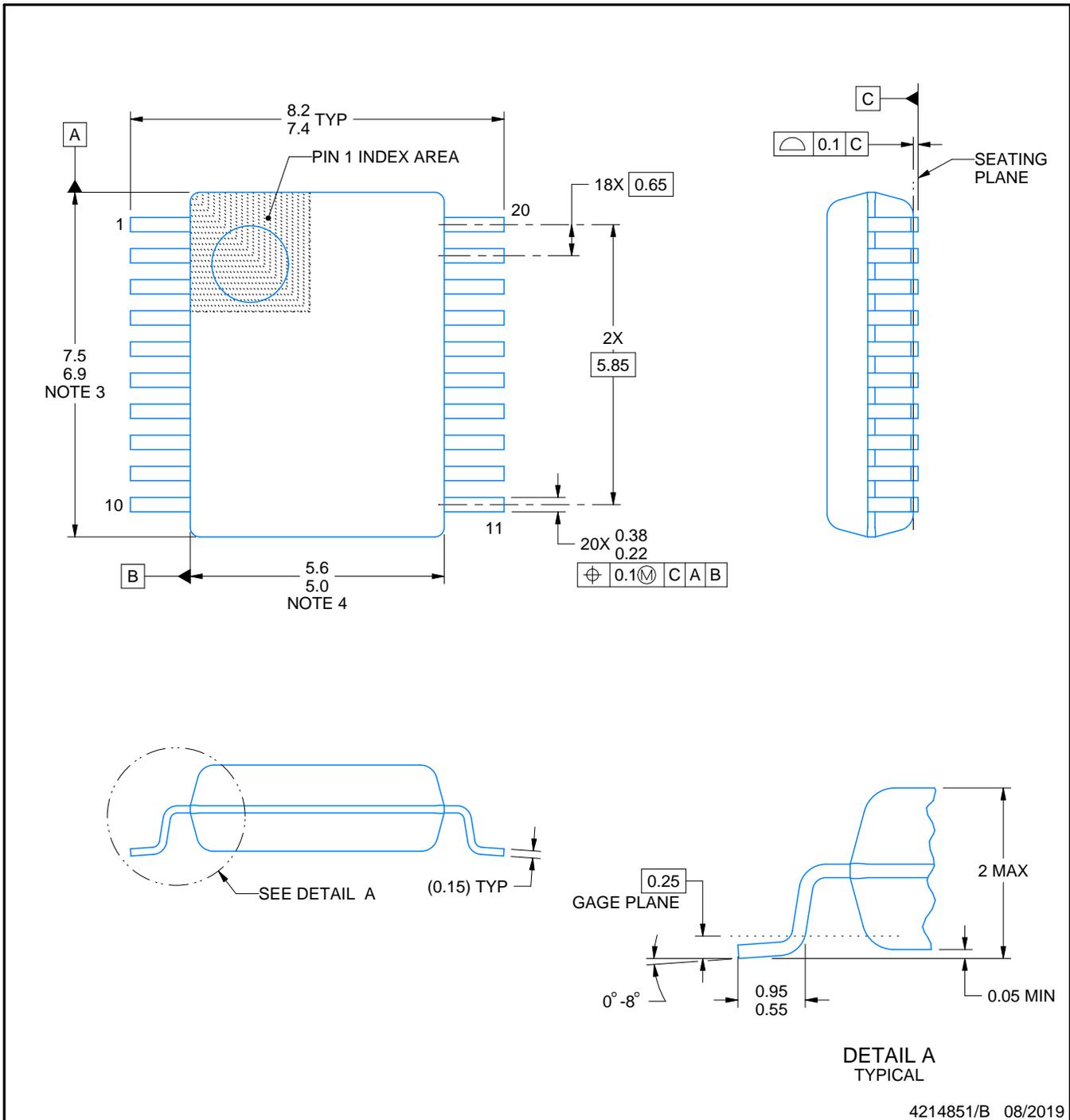
4214851/B   08/2019

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.

20X (1.85)

1

20X (0.45)

SYMM

(R0.05) TYP

20

18X (0.65)

SYMM

10

11

(7)
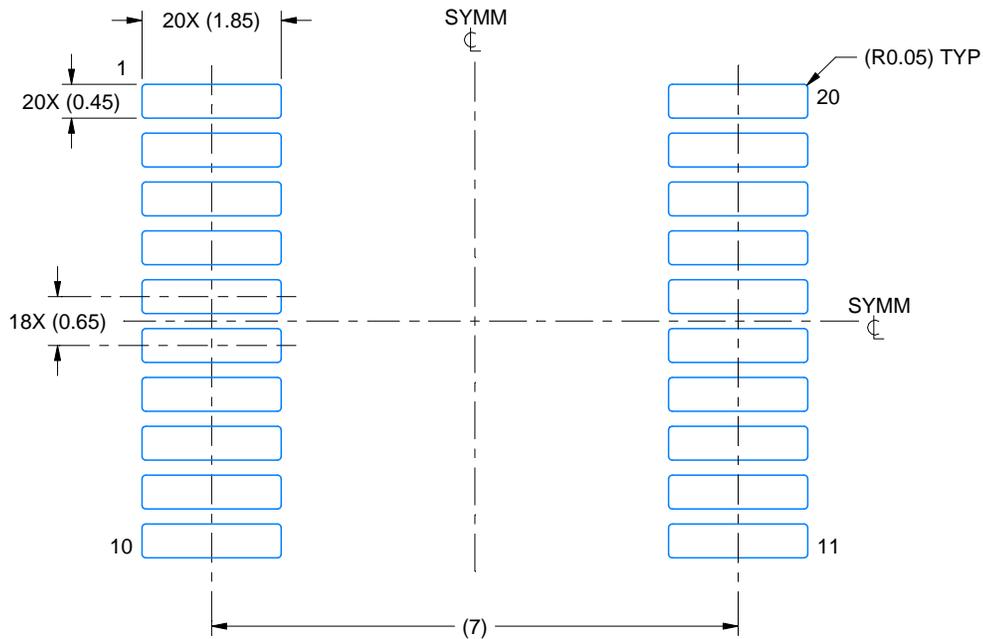
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X
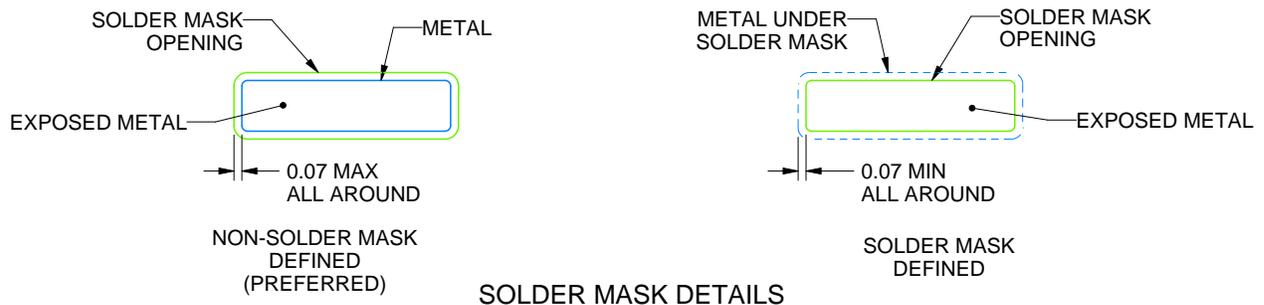
SOLDER MASK
OPENING

METAL

EXPOSED METAL

0.07 MAX
ALL AROUND

NON-SOLDER MASK
DEFINED
(PREFERRED)

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

EXPOSED METAL

0.07 MIN
ALL AROUND

SOLDER MASK
DEFINED

SOLDER MASK DETAILS

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NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

20X (1.85)

SYMM

1

(R0.05) TYP

20X (0.45)

20

18X (0.65)

SYMM

10

11

(7)

SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4214851/B   08/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate
   design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PW (R−PDSO−G20)   PLASTIC SMALL OUTLINE
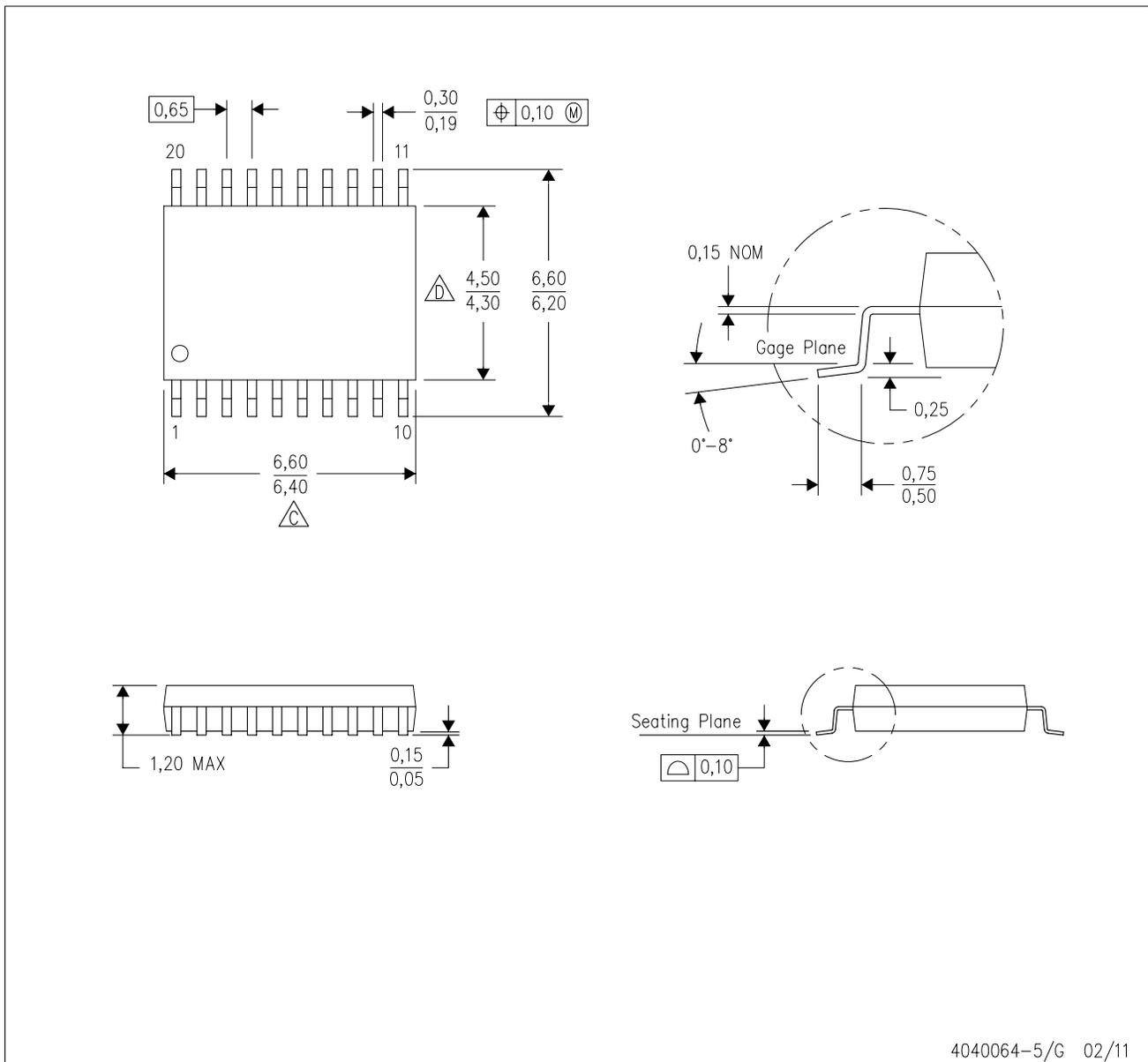
4040064−5/G 02/11

NOTES: A.   All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M−1994.
         B.   This drawing is subject to change without notice.
         C.   Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
         D.   Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
         E.   Falls within JEDEC MO−153

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PW (R−PDSO−G20)   PLASTIC SMALL OUTLINE

Example Board Layout

Based on a stencil thickness
of .127mm (.005inch).

18x0,65

20x0,25

1,55

5,6

5,6

18x0,65

Example
Non Soldermask Defined Pad

Example
Solder Mask Opening
(See Note E)

0,3

1,6

Pad Geometry

0,07
All Around

4211284−5/G   08/15
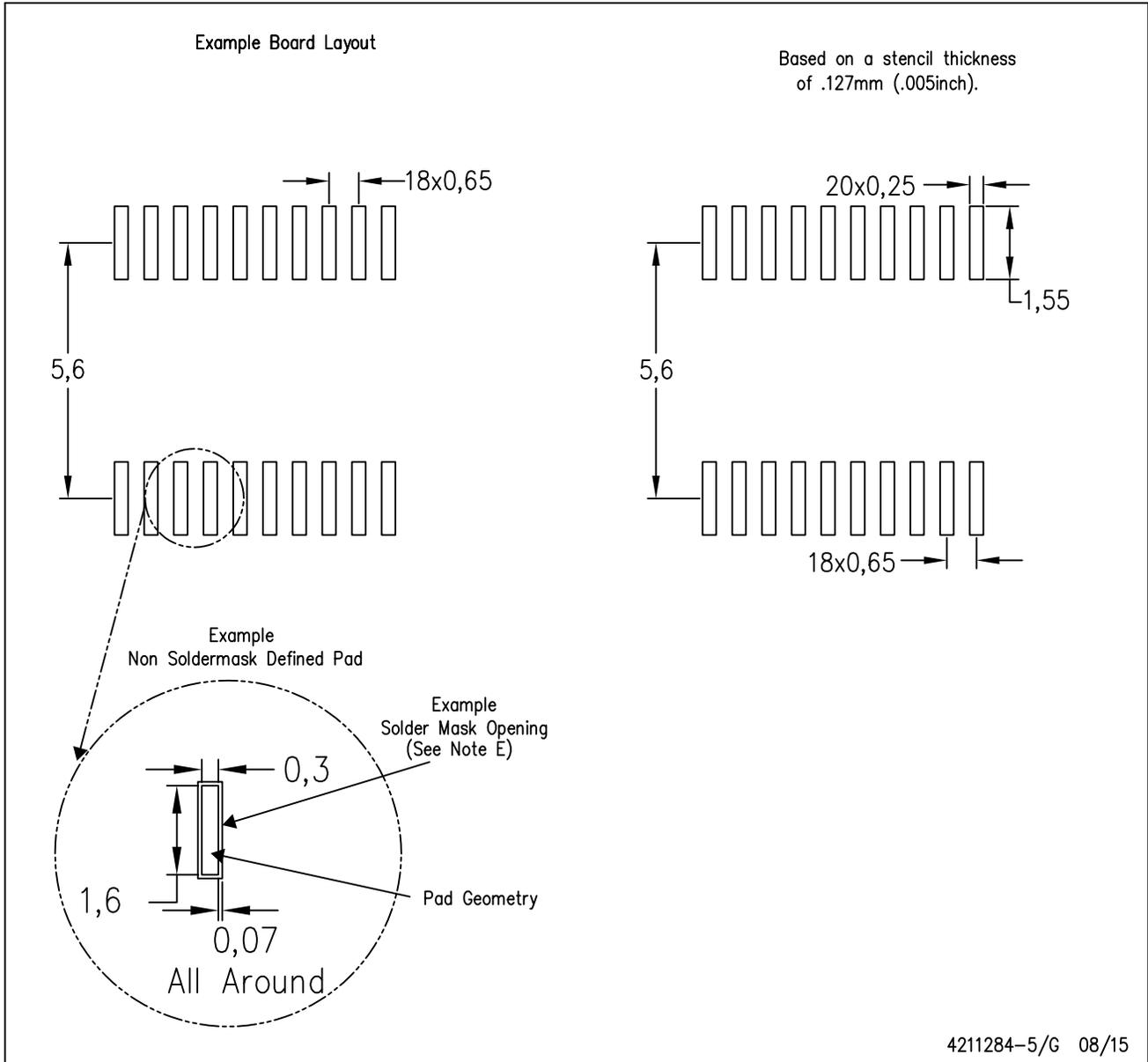
NOTES: A.   All linear dimensions are in millimeters.
         B.   This drawing is subject to change without notice.
         C.   Publication IPC−7351 is recommended for alternate design.
         D.   Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should
              contact their board assembly site for stencil design recommendations. Refer to IPC−7525 for other stencil recommendations.
         E.   Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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C

SEATING PLANE

⌀ 0.1 C

10.63 / 9.97 TYP

A

PIN 1 ID AREA

1

20

18X 1.27

13.0 / 12.6 NOTE 3

2X 11.43

10

11

B

7.6 / 7.4 NOTE 4

20X 0.51 / 0.31

⊕ 0.25 Ⓜ C A B

2.65 MAX

0.33 / 0.10 TYP

SEE DETAIL A

0.25 GAGE PLANE

0° - 8°

1.27 / 0.40

0.3 / 0.1

DETAIL A
TYPICAL
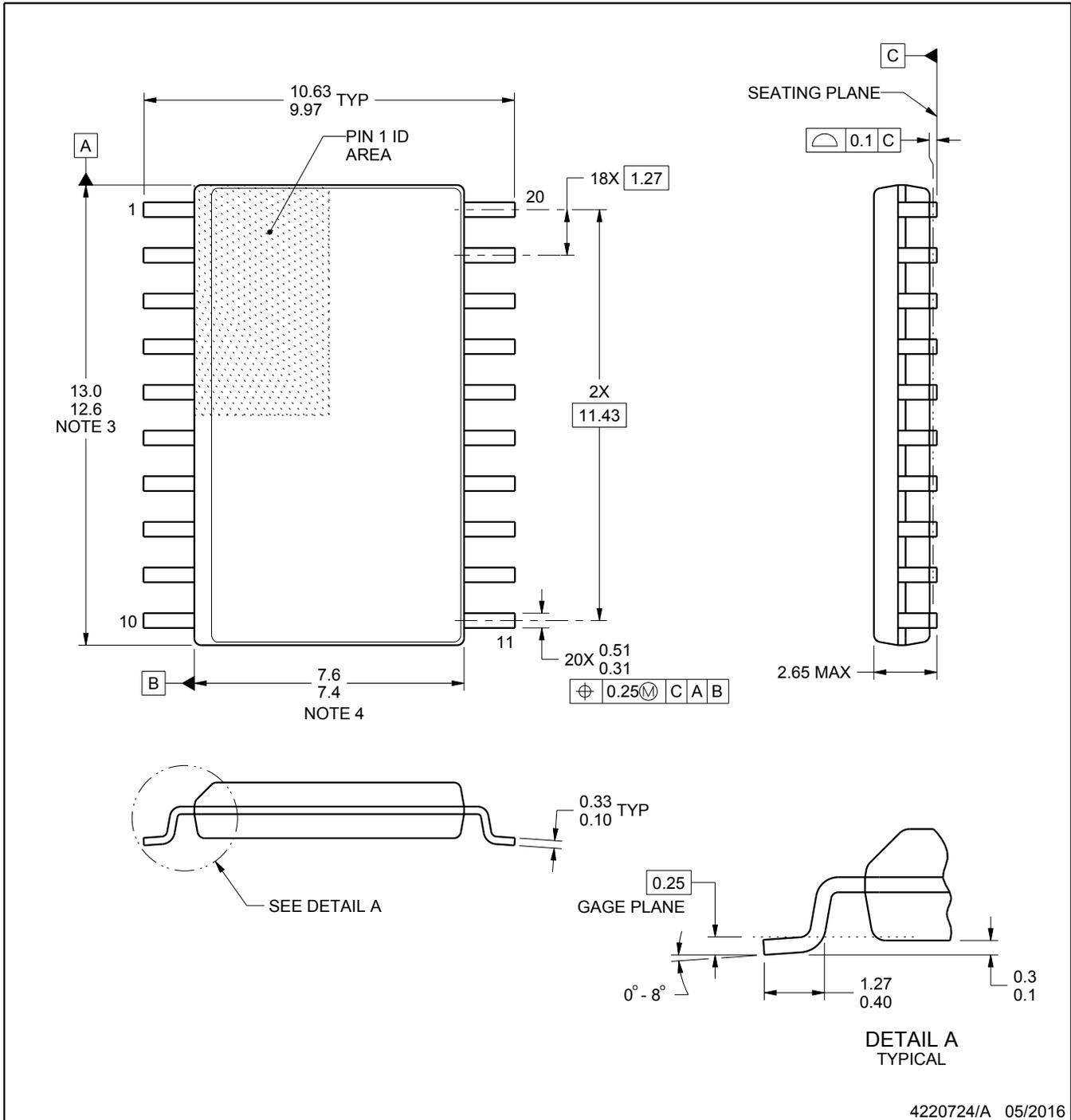
4220724/A 05/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

20X (2)

SYMM
℄

1

20X (0.6)

20

18X (1.27)

SYMM
℄

(R0.05)
TYP

10

11

(9.3)
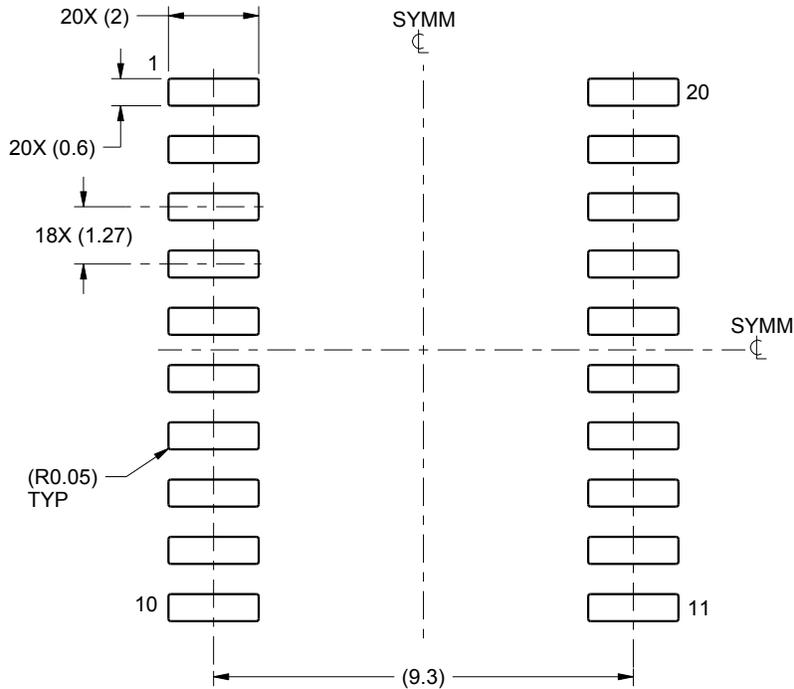
LAND PATTERN EXAMPLE
SCALE:6X

SOLDER MASK
OPENING

METAL

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

0.07 MAX
ALL AROUND

0.07 MIN
ALL AROUND

NON SOLDER MASK
DEFINED

SOLDER MASK
DEFINED
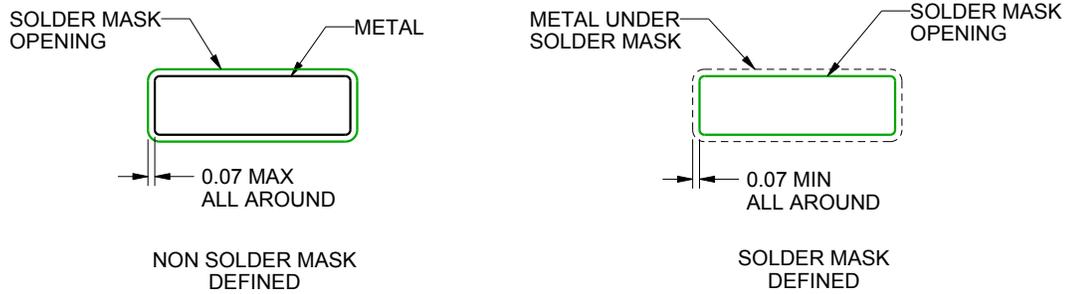
SOLDER MASK DETAILS

4220724/A   05/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

20X (2)

1

20X (0.6)

18X (1.27)

SYMM

SYMM

20

10

11

(9.3)
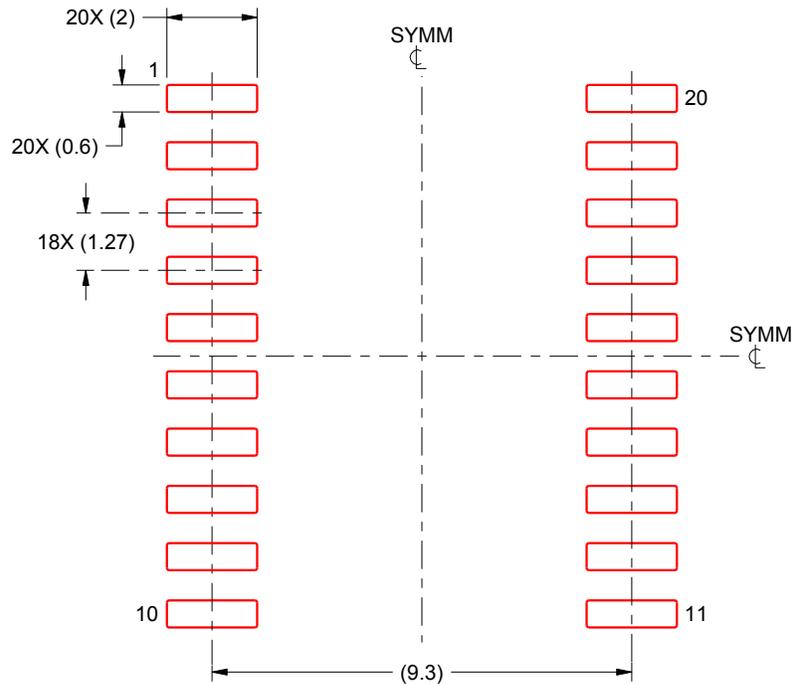
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A   05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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